

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,498,243 B2
APPLICATION NO. : 10/590223
DATED : March 3, 2009
INVENTOR(S) : Liu et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Specification

Col. 1, line 14: "filings 35 U.S.C." should read --filings under 35 U.S.C.--.

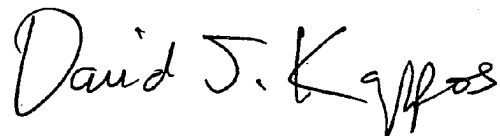
Col. 4, line 14: "layer pattened" should read --layer patterned--.

Col. 12, lines 64-66: "This first region 525 generally includes defects due to the lattice mismatch are substantially terminated." should read

--This first region 525 generally includes defects associated with a lattice mismatch at an interface between the germanium-based layer 524 and the bulk substrate 505 at the seed location 512. Upon a change in direction of growth to a generally horizontal direction in region 526 of the germanium-based layer 524, defects due to the lattice mismatch are substantially terminated.--.

Signed and Sealed this

Twenty-seventh Day of April, 2010

A handwritten signature in black ink, reading "David J. Kappos". The signature is written in a cursive, flowing style with a large, stylized 'D' and 'K'.

David J. Kappos
Director of the United States Patent and Trademark Office